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range of the acceleration voltage between 400V and 1000V so that the emission efficiency of secondary electrons emitted from the surface may exceed 1.

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Please replace the paragraph on page 27 lines 12–23 with the following:

FIG. 10C shows the relationship between the beam scan position and the secondary electron amount. As is shown in FIG. 10C, the amount of secondary electrons increases in a region of the center position x_1 of the underlying mark 104, where the surface potential is low, that is, in a region which is negatively charged. However, the amount of secondary electrons decreases in a region of the position x_2 distanced from the center position x_1 in the beam scan direction, where the surface potential is relatively high. The decreasing amount of secondary electrons are observed as a dark portion if they are detected by the detector 107 (not shown).

IN THE CLAIMS:

Please amend claims 6 and 16, and add new claims 23 and 24, as follows:

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6. (Amended) A pattern observation apparatus for observing a pattern by radiating a charged particle beam on a sample in which the pattern is formed on a substrate, the apparatus comprising:

a first beam radiation section for performing a first charged particle beam radiation on a sample in which a pattern is formed on a substrate and a surface of the substrate including the pattern is covered with an insulating film whose surface is flat including the pattern, and charging a surface of the sample;